

# Hi3516C V500 DDR4 Configuration Guide

Issue 01

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## **About This Document**

## **Related Version**

The following table lists the product version related to this document.

Product Name	Version
Hi3516C	V500

## **Intended Audience**

This document is intended for:

- Technical support engineers
- Software development engineers

# **Change History**

Changes between document issues are cumulative. The latest document issue contains all the changes made in earlier issues.

#### Issue 01 (2019-05-25)

This issue is the first official release.



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# 1 DDR4 Driver Configuration

## 1.1 CLK/AC Driver Configuration

- Register address
  - DDR PHY: 0x1206d018
- Register description
  - Bit[25:23]: CK driver
  - Bit[22:20]: 2T driver
  - Bit[19:17]: 1T driver
- Drive strength
  - 000: disabled
  - 001: 240 ohms
  - 010: 120 ohms
  - 011: 80 ohms
  - 100: 60 ohms
  - 101: 48 ohms
  - 110: 40 ohms
  - 111: 34 ohms

#### ■ NOTE

The 1T signals refer to CKE, CSN, ODT, and RESET signals, while the 2T signals refer to the AC signals except 1T signals.

## 1.2 DQS/DQ Driver Configuration in the Write Direction

- Register address
  - DDR PHY: 0x1206d204 (bytes 0–1)
- Register description
  - Bit[16:14]: DQS driver in the write direction
  - Bit[13:11]: DQ driver in the write direction
- Drive strength
  - 000: disabled

- 001: 240 ohms

- 010: 120 ohms

- 011: 80 ohms

- 100: 60 ohms

- 101: 48 ohms

- 110: 40 ohms

- 111: 34 ohms

## 1.3 DQS/DQ Driver Configuration in the Read Direction

Register address

DDR PHY: 0x1206c064

• Register description

Bit[18] and bit[17]: DQS/DQ driver in the read direction

Drive strength

- 00: 34 ohms

- 01: 48 ohms

- 10: reserved

- 11: reserved

# 2 DDR4 ODT Configuration

## 2.1 DQS/DQ ODT Configuration in the Write Direction

### 2.1.1 ODT Enable in the Write Direction

Register address

DDRC: 0x120680a0

- Register description
  - Bit[0] = 0: ODT disabled in the write direction
  - Bit[0] = 1: ODT enabled in the write direction

#### 2.1.2 ODT in the Write Direction

Register address

DDR PHY: 0x1206c064

- Register description
  - Bit[26:24]: DQS/DQ ODT configuration in the write direction
- ODT values in the write direction

- 000: Disable

- 001: 60 ohms

- 010: 120 ohms

- 011: 40 ohms

- 100: 240 ohms

- 101: 48 ohms

- 110: 80 ohms

- 111: 34 ohms



The ODT configuration in the write direction takes effect for both DQS and DQ signals.

# 2.2 DQS/DQ ODT Configuration in the Read Direction

## 2.2.1 ODT Enable in the Read Direction

Register address

DDR PHY: 0x1206d248 (bytes 0-1)

- Register description
  - Bit[3] = 0: ODT enabled in the read direction
  - Bit[3] = 1: ODT disabled in the read direction

### 2.2.2 ODT Values in the Read Direction

Register address

DDR PHY: 0x1206d204 (bytes 0-1)

- Register description
  - Bit[31:29]: DQS ODT in the read direction
  - Bit[28:26]: DQ ODT in the read direction
- ODT values in the read direction
  - 000: disabled
  - 001: 240 ohms
  - 010: 120 ohms
  - 011: 80 ohms
  - 100: 60 ohms
  - 101: 48 ohms
  - 110: 40 ohms
  - 111: 34 ohms

# 3 DDR4 Capacity Configuration

## 3.1 U-Boot Table Overview

The Hi3516C V500 memory interface can connect to a DDR4 DRAM with a maximum data bit width of 16 bits in single-channel mode. The DDR configuration is implemented in the U-Boot table. Hi3516C V500 provides one DDR4 U-Boot table, corresponding to the DDR4 DMEB design scheme.

DDR4 DMEB U-Boot table: Hi3516CV500-DDR4DMEB\_4L-DDR4\_1800M\_1GB\_16bit-A7\_900M-SYSBUS\_300M

Table 3-1 lists the DDR specifications supported by the U-Boot tables.

**Table 3-1** DDR specifications supported by the U-Boot tables

U-Boot Table	Total Capacity/Total Bit Width	Channel	DDR Type	DDR Rate (Mbit/s)	Rank Count	DDR Bit Width (Bit Width/PCS x Count)	Capacity/ PCS
DDR4D MEB U-Boot table	512 MB/16 bits or 1 GB/16 bits	Channel 0	DDR4	1800	1	16 bits x 1	4 Gbits or 8 Gbits

M NOTE

The DDR4DMEB U-Boot table is compatible with the single-piece 8 Gbits or 4 Gbits DDR. You do not need to modify the configuration.